

AMENDMENT TO THE CLAIMS:

1. (Currently Amended) A semiconductor device comprising:  
a switching thin film transistor which operates by receiving a gate signal at its gate  
and for reading a data signal; and  
an element driving thin film transistor provided between a driving power supply and  
an element to be driven, for controlling the power supplied from said driving power supply to  
said element to be driven based on a data signal supplied from said switching thin film  
transistor; characterized in that  
wherein a compensation thin film transistor having an opposite conductive  
characteristic with respect to said element driving thin film transistor is provided between  
said driving power supply and said element driving thin film transistor,  
wherein a gate and either a source or a drain of said compensation thin film transistor  
are connected, and said compensation thin film transistor is connected between said driving  
power supply and said element driving thin film transistor.

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2. (Cancelled)

3. (Original) A semiconductor device according to claim 1, wherein said element  
driving thin film transistor comprises a plurality of thin film transistors connected to each  
other in parallel.

4. (Original) A semiconductor device according to claim 3, wherein said  
compensation thin film transistor is a diode connected transistor connected between said  
driving power supply and said element driving thin film transistor.

5. (Original) A semiconductor device according to claim 1, wherein  
said element driving thin film transistor comprises a plurality of thin film transistors  
connected between said driving power supply and said element to be driven and in parallel to  
each other; and  
said compensation thin film transistor is respectively provided between said plurality  
of thin film transistors connected in parallel and said driving power supply.

6. (Original) A semiconductor device according to claim 5, wherein said  
compensation thin film transistor is a diode connected transistor connected between said  
driving power supply and said element driving thin film transistor.

7. (Original) A semiconductor device according to claim 1, wherein said element to  
be driven is an electroluminescence element which includes an emissive layer between a first  
electrode and a second electrode.

8. (Original) A semiconductor device according to claim 6, wherein said electroluminescence element is an organic electroluminescence element which employs an organic compound in an emissive layer.

9. (Original) A semiconductor device according to claim 1, wherein said semiconductor device is used for an active matrix type display device wherein each of the pixels arranged in a matrix form comprises said switching thin film transistor, said element driving thin film transistor, said compensation thin film transistor, and said element to be driven as a display element.

10. (Currently Amended) A semiconductor device comprising:  
a switching thin film transistor which operates by receiving a gate signal at its gate  
and for reading a data signal; and  
an element driving thin film transistor provided between a driving power supply and  
an element to be driven, for controlling the power supplied from said driving power supply to  
said element to be driven based on a data signal supplied from said switching thin film  
transistor;

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wherein a compensation thin film transistor having an opposite conductive  
characteristic with respect to said element driving thin film transistor is provided between  
said driving power supply and said element driving thin film transistor.  
A semiconductor device according to claim 1, wherein said element driving thin film transistor and said compensation thin film transistor are placed so that the channel length direction of said thin film transistors is along the extension direction of the data line for supplying said data signal to said switching thin film transistor.

11. (Currently Amended) A semiconductor device comprising:  
a switching thin film transistor which operates by receiving a gate signal at its gate  
and for reading a data signal; and  
an element driving thin film transistor provided between a driving power supply and  
an element to be driven, for controlling the power supplied from said driving power supply to  
said element to be driven based on a data signal supplied from said switching thin film  
transistor;  
wherein a compensation thin film transistor having an opposite conductive  
characteristic with respect to said element driving thin film transistor is provided between  
said driving power supply and said element driving thin film transistor.  
A semiconductor device according to claim 1, wherein the channel length direction of said element driving thin

film transistor does not coincide with the channel length direction of said switching thin film transistor.

12. (Currently Amended) A semiconductor device comprising:  
a switching thin film transistor which operates by receiving a gate signal at its gate  
and for reading a data signal; and  
an element driving thin film transistor provided between a driving power supply and  
an element to be driven, for controlling the power supplied from said driving power supply to  
said element to be driven based on a data signal supplied from said switching thin film  
transistor;

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wherein a compensation thin film transistor having an opposite conductive  
characteristic with respect to said element driving thin film transistor is provided between  
said driving power supply and said element driving thin film transistor.  
A semiconductor device according to claim 1, wherein

said element driving thin film transistor is formed so that its channel length direction is along the scan direction of a line pulse laser for annealing the channel region of the transistor.

13. (Original) A semiconductor device according to claim 12, wherein a gate and either a source or a drain of said compensation thin film transistor are connected, and said compensation thin film transistor is connected between said driving power supply and said element driving thin film transistor.